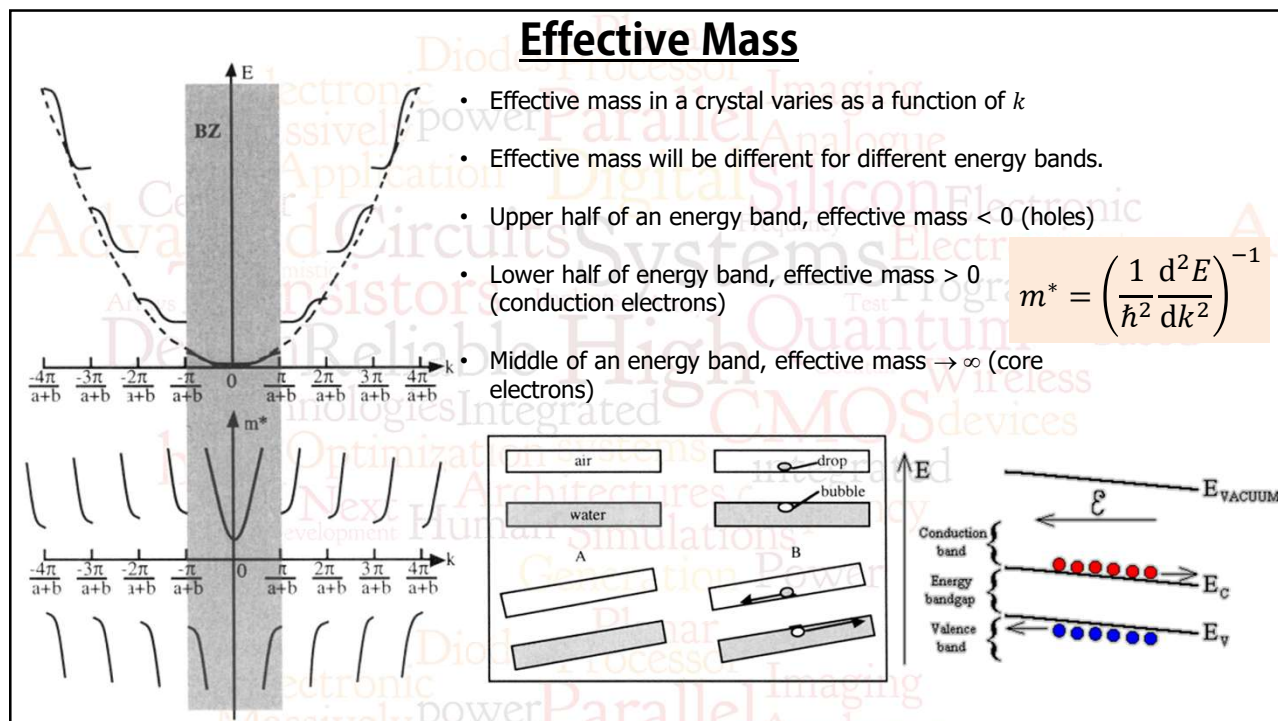


## Effective Mass



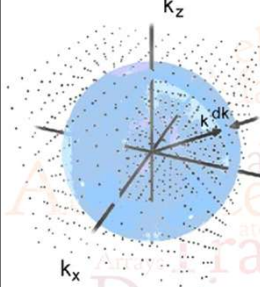
40

## Electronic Properties

| Electronic Properties |             |            |       |                            |                          |                      |   |                                |                   |                   |
|-----------------------|-------------|------------|-------|----------------------------|--------------------------|----------------------|---|--------------------------------|-------------------|-------------------|
| Material              | Transition  | Gap energy |       | Room-temp.<br>conductivity | Mobility of<br>electrons | Mobility of<br>holes | Work function<br>(photoelectric)<br>$\phi$ [eV] | Effective mass<br>ratio at 4 K |                   |                   |
|                       |             | $E_g$ [eV] |       |                            |                          |                      |   | $m_e^*$                        | $m_h^*$           |                   |
|                       |             | 0 K        | 300 K |                            |                          |                      |   | $m_0$                          | $m_0$             |                   |
| Element               | C (diamond) | I          | 5.48  | 5.47                       | $10^{-12}$               | 0.18                 | 0.12  | 4.8                            | 0.2               | 0.25              |
|                       | Ge          | I          | 0.74  | 0.66                       | 2.2                      | 0.39                 | 0.19  | 4.6                            | 1.64 <sup>a</sup> | 0.04 <sup>c</sup> |
|                       |             |            |       |                            |                          |                      |   |                                | 0.08 <sup>b</sup> | 0.28 <sup>d</sup> |
|                       | Si          | I          | 1.17  | 1.12                       | $9 \times 10^{-4}$       | 0.15                 | 0.045   | 3.6                            | 0.98 <sup>a</sup> | 0.16 <sup>c</sup> |
|                       |             |            |       |                            |                          |                      |   |                                | 0.19 <sup>b</sup> | 0.49 <sup>d</sup> |
|                       | Sn (gray)   | D          | 0.09  | 0.08                       | $10^6$                   | 0.14                 | 0.12  | 4.4                            |                   | 0.3 <sup>d</sup>  |
| III-V                 | GaAs        | D          | 1.52  | 1.42                       | $10^{-6}$                | 0.85                 | 0.04  |                                | 0.067             | 0.082             |
|                       | InAs        | D          | 0.42  | 0.36                       | $10^4$                   | 3.30                 | 0.046   | 4.9                            | 0.023             | 0.40              |
|                       | InSb        | D          | 0.23  | 0.17                       |                          | 8.00                 | 0.125   |                                | 0.014             | 0.40              |
|                       | GaP         | I          | 2.34  | 2.26                       |                          | 0.01                 | 0.007   |                                | 0.82              | 0.60              |
|                       | GaN         | D          | 3.50  | 3.36                       |                          | 0.04                 | 0.01  |                                | 0.19              | 0.60              |
|                       | InN         | D          |       | 0.7                        |                          |                      |   |                                |                   |                   |
|                       | InP         | D          | 1.42  | 1.35                       |                          | 0.46                 | 0.015   |                                | 0.077             | 0.64              |

41

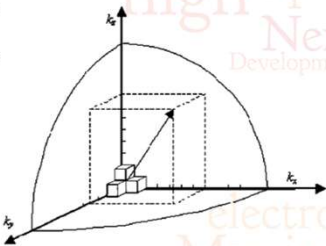
## Density of States



The Density of States (DOS) is essentially the number of different states at a particular energy level that electrons are allowed to occupy, i.e. the number of electron states per unit volume per unit energy.

Bulk properties such as specific heat, paramagnetic susceptibility, and other transport phenomena of conductive solids depend on this function.

DOS calculations allow one to determine the general distribution of states as a function of energy and can also determine the spacing between energy bands in semiconductors



$$g_C(E)_{3D} = \frac{1}{2\pi^2} \left( \frac{2m_e^*}{\hbar^2} \right)^{\frac{3}{2}} (E - E_C)^{\frac{1}{2}}$$